TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7SH32FE

#### 2 Input OR Gate

#### **Features**

• Super high speed operation :tpD = 3.8 ns (typ.)

 $@V_{CC} = 5 V$ 

• Low power dissipation :  $I_{CC} = 2 \mu A (Max.)$ 

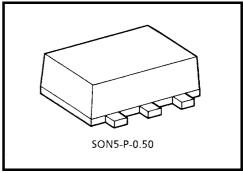
@ Ta = 25°C

• High noise immunity :  $V_{NIH} = V_{NIH}$ 

= 28% V<sub>CC</sub> (Min.)

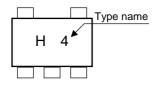
• 5.5V tolerant input.

• Wide operation voltage range : VCC (opr) = 2~5.5 V

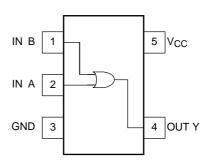


Weight: 0.003 g (typ.)

#### Marking



#### Pin Assignment (top view)



#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7	V
DC input voltage	V <sub>IN</sub>	-0.5~7	V
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	l <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	P <sub>D</sub>	150	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## **Logic Diagram**

# Logic Diagram



#### **Truth Table**

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

### **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~ V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~100 ( $V_{CC}$ = 3.3 V $\pm$ 0.3 V )	ns/V	
	ui/uv	0~20 ( $V_{CC}$ = 5 $V$ ± 0.5 $V$ )		

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics   Symbol		Test	Toot	Condition		Ta = 25°C			Ta = -40~85°C		Unit
		Circuit	Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
High lovel input		_		2.0	1.5	_	_	1.5	_	V	
High-level input voltage VIH —				_	3.0~5.5	V <sub>CC</sub> × 0.7		_	V <sub>CC</sub> × 0.7		
Low lovel input					2.0	_		0.5	_	0.5	V
Low-level input voltage V <sub>IL</sub> —	_		_	3.0~5.5		l	V <sub>CC</sub> × 0.3		V <sub>CC</sub> × 0.3		
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	_	1.9		V
	High-level output voltage	_			3.0	2.9	3.0	_	2.9		
					4.5	4.4	4.5	_	4.4		
				$I_{OH} = -4 \text{ mA}$	3.0	2.58		_	2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94		_	3.80		
				2.0	_	0	0.1	_	0.1		
	Low-level output voltage		$V_{IN} = V_{IL}$	$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	V
Low-level output voltage		_			4.5	_	0	0.1	_	0.1	
			I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44		
			I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44		
Input leakage current	I <sub>IN</sub>	_	V <sub>IN</sub> = 5.5 V or GND		0~5.5	_		±0.1		±1.0	μΑ
Quiescent supply current	Icc	_	$V_{IN} = V_{CC}$	or GND	5.5	_	_	2.0	_	20.0	μΑ

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#### AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		- Unit
			V <sub>CC</sub> (V)	C <sub>L (</sub> pF)	Min	Тур.	Max	Min	Max	Offic
Propagation delay time	tPLH tPHL		3.3 ± 0.3	15	_	5.5	7.9	1.0	9.5	ns
				50	_	8.0	11.4	1.0	13.0	
				15	_	3.8	5.5	1.0	6.5	
		5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5		
Input capacitance	C <sub>IN</sub>				_	4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>		(Note)		_	15	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

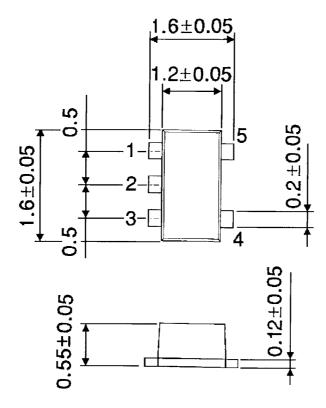
Average operating current can be obtained by the equation.

$$I_{CC\;(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

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### **Package Dimensions**

SON5-P-0.50 Unit: mm



Weight: 0.003 g (typ.)

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